BLF8G20LS-220

Power LDMOS transistor

Rev. 2 — 30 May 2013 Product data sheet

1. Product profile

1.1 General description

220 W LDMOS power transistor for base station applications at frequencies from 1800 MHz to 2000 MHz.

Table 1. Typical performance

Typical RF performance at T_{case} = 25 °C in a common source class-AB production test circuit.

Test signal	f	I_{Dq}	V_{DS}	$P_{L(AV)}$	G_p	η_D	ACPR
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	1805 to 1880	1600	28	55	18.9	34	–31 [1]

[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF; carrier spacing 5 MHz.

1.2 Features and benefits

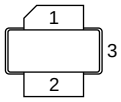
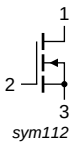
- Excellent ruggedness
- High efficiency
- Low R_{th} providing excellent thermal stability
- Designed for broadband operation
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- RF power amplifiers for W-CDMA base stations and multi carrier applications in the 1800 MHz to 2000 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
1	drain			
2	gate			
3	source	[1]		

sym112

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF8G20LS-220	-	earless flanged ceramic package; 2 leads	SOT502B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage			-	65	V
V_{GS}	gate-source voltage			−0.5	+13	V
T_{stg}	storage temperature			−65	+150	°C
T_j	junction temperature		[1]	-	225	°C

[1] Continuous use at maximum temperature will affect the reliability.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	T_{case} = 80 °C; P_L = 55 W; V_{DS} = 28 V; I_{Dq} = 1600 mA	0.27	K/W

6. Characteristics

Table 6. DC characteristics

T_j = 25 °C, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 2.7 mA	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_D = 270 mA	1.5	1.9	2.3	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 28 V; I_D = 1.6 A	1.7	2.1	2.5	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	4.2	µA
I_{DSX}	drain cut-off current	V_{GS} = $V_{GS(th)}$ + 3.75 V; V_{DS} = 10 V	-	50.6	-	A
I_{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	420	nA
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 13.5 A	-	19.6	-	S
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = $V_{GS(th)}$ + 3.75 V; I_D = 9.45 A	-	0.057	-	Ω

Table 7. RF characteristics

Test signal: 2-carrier W-CDMA; PAR = 8.4 dB at 0.01 % probability on CCDF; 3GPP test model 1; 64 DPCH; f_1 = 1807.5 MHz; f_2 = 1812.5 MHz; f_3 = 1872.5 MHz; f_4 = 1877.5 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 1600 mA; T_{case} = 25 °C; unless otherwise specified; in a production circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	$P_{L(AV)}$ = 55 W	17.8	18.9	-	dB
η_D	drain efficiency	$P_{L(AV)}$ = 55 W	29	34	-	%
RL_{in}	input return loss	$P_{L(AV)}$ = 55 W	-	–15.5	–7	dB
ACPR	adjacent channel power ratio	$P_{L(AV)}$ = 55 W	-	–31	–26	dBc

7. Test information

7.1 Ruggedness in class-AB operation

The BLF8G20LS-220 is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 1600 mA; P_L = 200 W (CW); f = 1805 MHz.

7.2 Impedance information

Table 8. Typical impedance

Measured load-pull data; I_{Dq} = 1600 mA; V_{DS} = 28 V.

f	Z_S[1]	Z_L[1]
(MHz)	(Ω)	(Ω)
1805	1.38 – j3.45	0.90 – j2.50
1843	1.43 – j3.63	0.82 – j2.37
1880	1.38 – j3.56	0.90 – j2.60

[1] Z_S and Z_L defined in Figure 1.

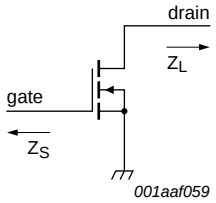
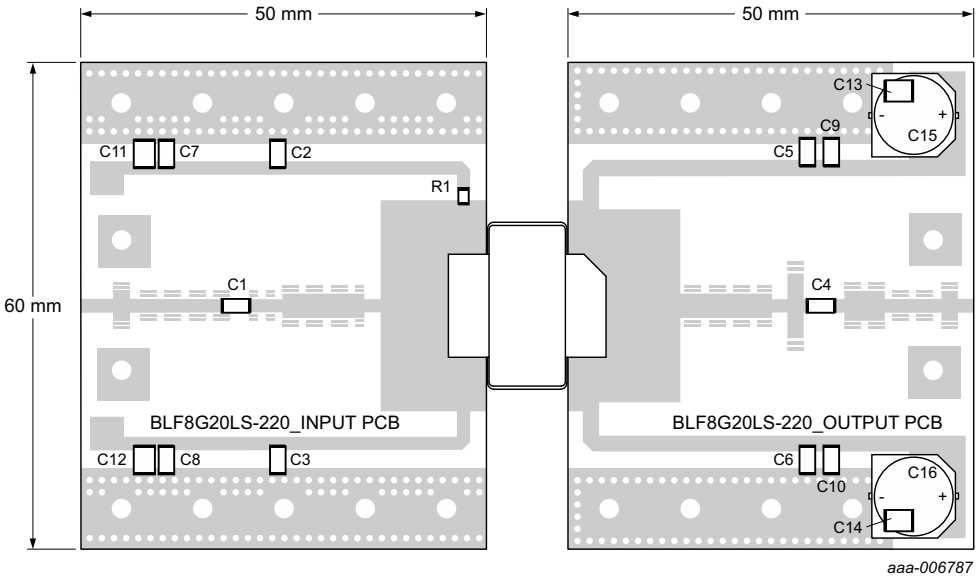


Fig 1. Definition of transistor impedance

7.3 Test circuit



See Table 9 for list of components.

Fig 2. Component layout

Table 9. List of components

See Figure 2 for component layout.
The used PCB material is Rogers RO4350B with a thickness of 0.76 mm.

Component	Description	Value		Remarks
C1, C2, C3, C4, C5, C6	multilayer ceramic chip capacitor	33 pF	[1]	ATC100B
C7, C8, C9, C10	multilayer ceramic chip capacitor	1 μF	[2]	TDK
C11, C12, C13, C14	multilayer ceramic chip capacitor	10 μF	[3]	Murata
C15, C16	multilayer ceramic chip capacitor	470 μF, 63 V		
R1	chip resistor	9.1 Ω		SMD 0805

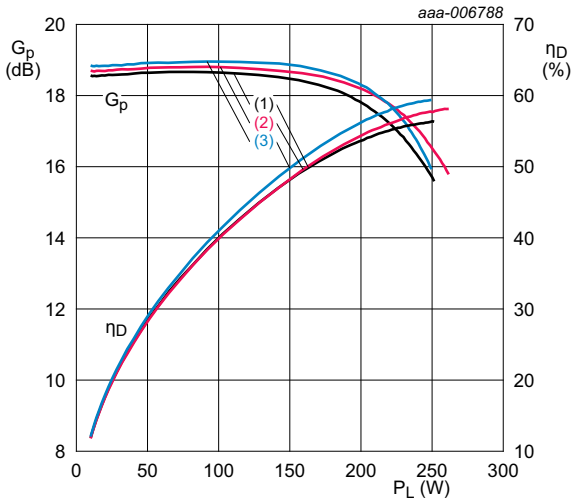
[1] American Technical Ceramics type 100B or capacitor of same quality.

[2] TDK or capacitor of same quality.

[3] Murata or capacitor of same quality.

7.4 Graphical data

7.4.1 CW pulse



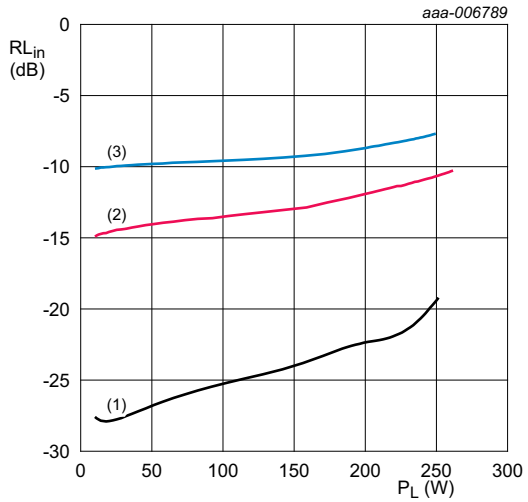
V_{DS} = 28 V; I_{Dq} = 1600 mA; t_p = 100 µs; δ = 10 %.

(1) f = 1805 MHz

(2) f = 1843 MHz

(3) f = 1880 MHz

Fig 3. Power gain and drain efficiency as function of output power; typical values



V_{DS} = 28 V; I_{Dq} = 1600 mA; t_p = 100 µs; δ = 10 %.

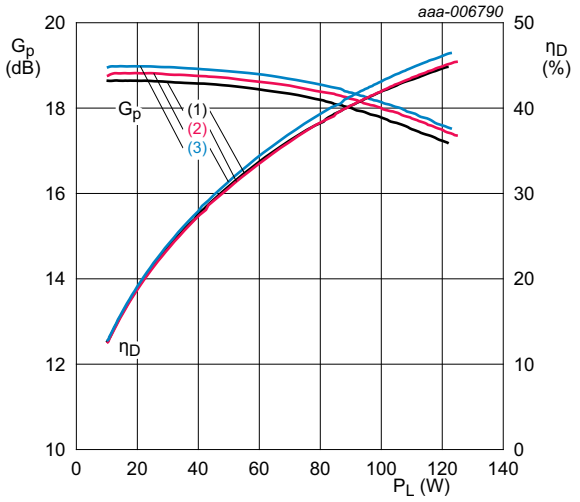
(1) f = 1805 MHz

(2) f = 1843 MHz

(3) f = 1880 MHz

Fig 4. Input return loss as a function of output power; typical values

7.4.2 1-Carrier W-CDMA



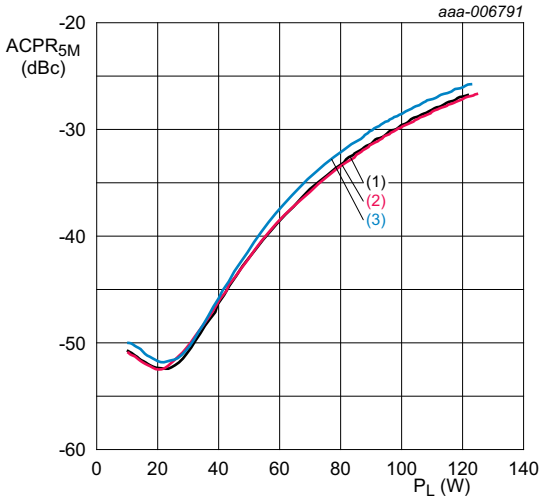
V_{DS} = 28 V; I_{Dq} = 1600 mA.

(1) f = 1805 MHz

(2) f = 1843 MHz

(3) f = 1880 MHz

Fig 5. Power gain and drain efficiency as function of output power; typical values



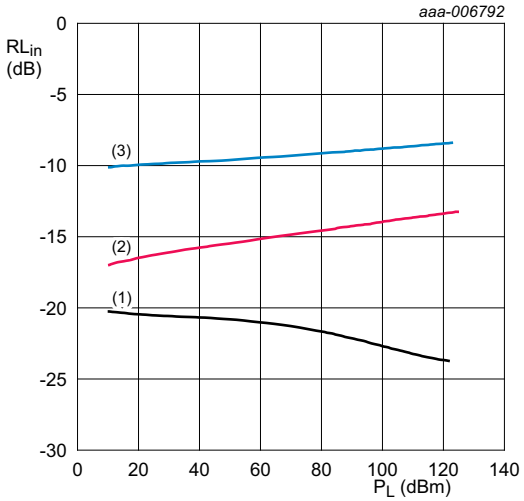
V_{DS} = 28 V; I_{Dq} = 1600 mA.

(1) f = 1805 MHz

(2) f = 1843 MHz

(3) f = 1880 MHz

Fig 6. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



V_{DS} = 28 V; I_{Dq} = 1600 mA.

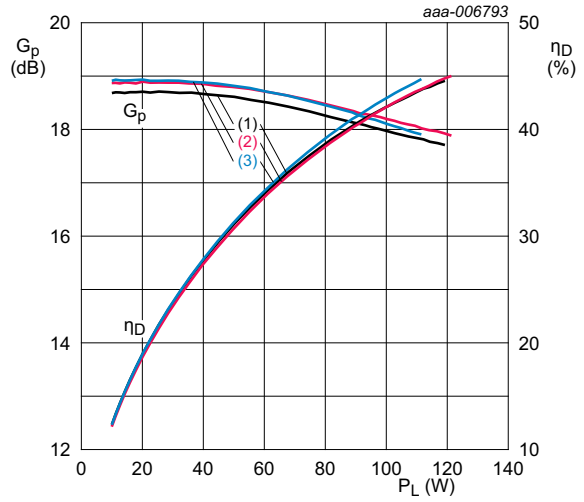
(1) f = 1805 MHz

(2) f = 1843 MHz

(3) f = 1880 MHz

Fig 7. Input return loss as a function of output power; typical values

7.4.3 2-Carrier W-CDMA



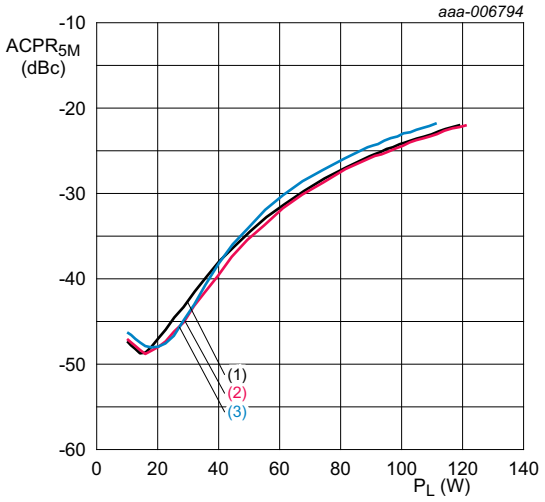
V_{DS} = 28 V; I_{Dq} = 1600 mA; f = 5 MHz; δ = 46 %.

(1) f = 1810 MHz

(2) f = 1843 MHz

(3) f = 1877.5 MHz

Fig 8. Power gain and drain efficiency as function of output power; typical values



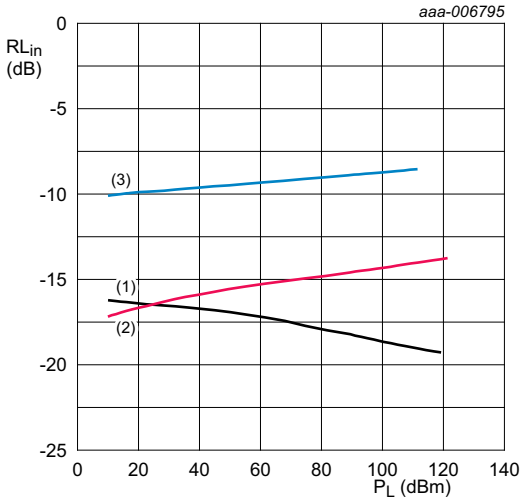
V_{DS} = 28 V; I_{Dq} = 1600 mA; f = 5 MHz; δ = 46 %.

(1) f = 1810 MHz

(2) f = 1843 MHz

(3) f = 1877.5 MHz

Fig 9. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



V_{DS} = 28 V; I_{Dq} = 1600 mA; f = 5 MHz; δ = 46 %.

(1) f = 1810 MHz

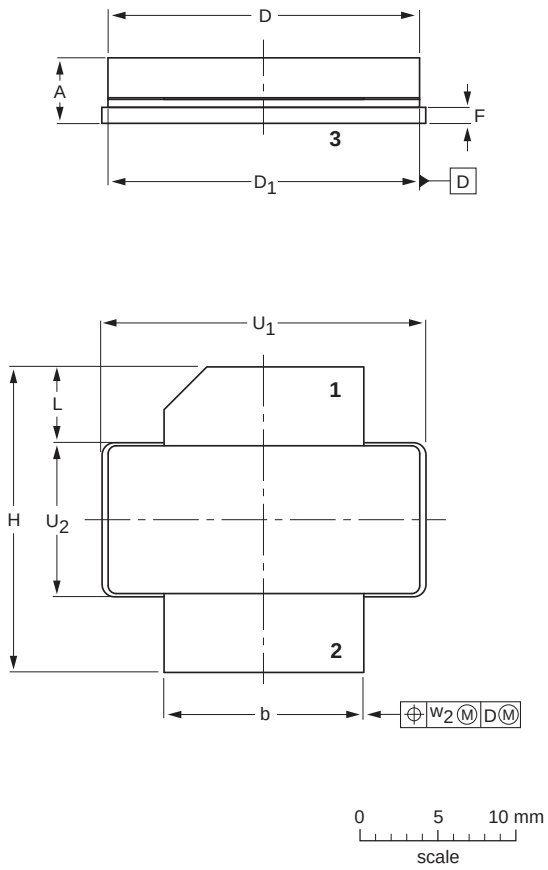
(2) f = 1843 MHz

(3) f = 1877.5 MHz

Fig 10. Input return loss as a function of output power; typical values

8. Package outline

Earless flanged ceramic package; 2 leads **SOT502B**



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D_1	E	E_1	F	H	L	Q	U_1	U_2	w_2
mm	4.72 3.43	12.83 12.57	0.15 0.08	20.02 19.61	19.96 19.66	9.50 9.30	9.53 9.25	1.14 0.89	19.94 18.92	5.33 4.32	1.70 1.45	20.70 20.45	9.91 9.65	0.25
inches	0.186 0.135	0.505 0.495	0.006 0.003	0.788 0.772	0.786 0.774	0.374 0.366	0.375 0.364	0.045 0.035	0.785 0.745	0.210 0.170	0.067 0.057	0.815 0.805	0.390 0.380	0.010

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT502B						~~07-05-09~~ 12-05-02

Fig 11. Package outline SOT502B

9. Handling information

CAUTION

This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 10. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF8G20LS-220 v.2	20130530	Product data sheet	-	BLF8G20LS-220 v.1
Modifications:	• Table 1 on page 1: table has been updated • Table 7 on page 3: table has been updated			
BLF8G20LS-220 v.1	20130307	Objective data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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14. Contents

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